

SMD Type

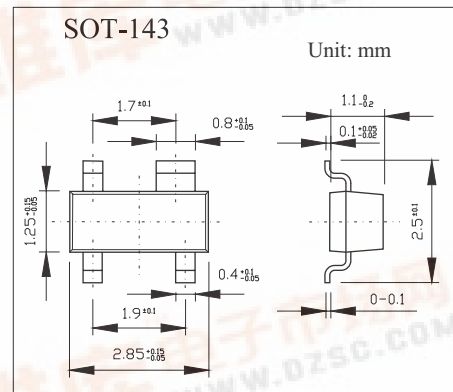
Diodes

Silicon Switching Diode Array

BAW100

■ Features

- For high-speed switching
- Electrically insulated diodes



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	75	V
Peak reverse voltage	V _{RM}	85	V
Forward current	I _F	200	mA
Surge forward current, t = 1 μs	I _{FS}	4.5	A
Total power dissipation, T _s = 31 °C	P _{tot}	330	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-65 to +150	°C
Junction - ambient ¹⁾	R _{th JA}	≤ 500	K/W
Junction - soldering point	R _{th JS}	≤ 360	K/W

Note

1.Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm² Cu

BAW100■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	V_{BR}	$I_{(BR)} = 100 \mu\text{A}$	85			V
Forward voltage	V_F	$I_F = 1 \text{ mA}$			715	mV
		$I_F = 10 \text{ mA}$			855	
		$I_F = 50 \text{ mA}$			1000	
		$I_F = 150 \text{ mA}$			1250	
Reverse current	I_R	$V_R = 75 \text{ V}$			1	μA
		$V_R = 25 \text{ V}, T_A = 150^\circ\text{C}$			30	
		$V_R = 75 \text{ V}, T_A = 150^\circ\text{C}$			50	
Diode capacitance	C_d	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			2	pF
Reverse recovery time	t_{rr}	$I_F = 10 \text{ mA}, I_R = 10 \text{ mA}, R_L = 100 \Omega$ measured at $I_R = 1 \text{ mA}$			6	ns

■ Marking

Marking	JSs
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